

Features

- Optimized for Broadband Operation (DC - 4 GHz)
- 25 W P3dB CW Power @ 3000 MHz
- 16 - 20 W P3dB CW Power from 1.0 - 2.5 GHz in application board with >45% Drain Efficiency
- 10 - 20 W P3dB CW Power from 0.03 - 1.0 GHz in application board with >50% Drain Efficiency
- High Efficiency from 14 to 28 V
- 4°C/W R_{TH} with $T_J < 200^\circ\text{C}$
- Robust up to 10:1 VSWR Mismatch at All Angles with No Device Damage at 90°C Flange
- Subject to EAR99 Export Control
- RoHS* Compliant

Applications

- Defense Communications
- Land Mobile Radio
- Avionics
- Wireless Infrastructure
- ISM
- VHF/UHF/L/S-Band Radar

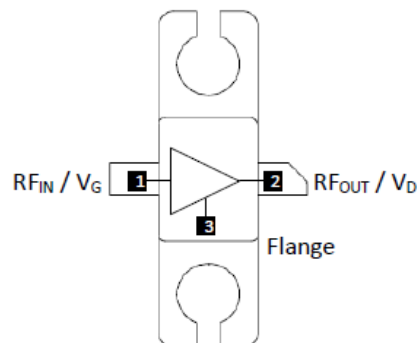
Description

The NPT1012B GaN HEMT is a power transistor optimized for DC - 4 GHz operation. This device supports CW, pulsed, and linear operation with output power levels to 25 W. This transistor is assembled in an industry standard surface mount plastic package.

Ordering Information

| Part Number | Package |
|-------------|--------------|
| NPT1012B | 30 slot tray |

Functional Schematic



Pin Configuration

| Pin # | Pin Name | Function |
|-------|---------------------|-------------------|
| 1 | RF_{IN} / V_G | RF Input / Gate |
| 2 | RF_{OUT} / V_D | RF Output / Drain |
| 3 | Flange ¹ | Ground / Source |

1. The flange must be connected to RF and DC ground. This path must also provide a low thermal resistance heat path.

* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

GaN Power Transistor, 28 V, 25 W DC - 4 GHz



NPT1012B

Rev. V1

Typical CW RF Specifications: (measured in a test fixture)

Freq. = 3 GHz, $V_{DS} = 28$ V, $I_{DQ} = 225$ mA, $T_C = 25^\circ\text{C}$

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Units |
|------------------------|---|------------------------|---------------------------------------|----------|------|-------|
| Average Output Power | 3 dB Compression 1 dB Compression | P_{3dB} P_{1dB} | 43 — | 44 43 | — | W |
| Small Signal Gain | — | G_{SS} | 12 | 13 | — | dB |
| Drain Efficiency | 3 dB Compression | η | 57 | 65 | — | % |
| Output Mismatch Stress | VSWR = 10:1. all phase angles, $P_{OUT} = P_{SAT}$ | ψ | No performance degradation after test | | | |

DC Electrical Characteristics: $T_C = 25^\circ\text{C}$

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Units |
|--------------------------------|---|-----------|------|------|------|----------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS} = -8$ V, $I_D = 8$ mA | V_{BDS} | 100 | — | — | V |
| Drain-Source Leakage Current | $V_{GS} = -8$ V, $V_{DS} = 60$ V | I_{DLK} | — | — | 4 | mA |
| On Characteristics | | | | | | |
| Gate Threshold Voltage | $V_{DS} = 28$ V, $I_D = 8$ mA | V_T | -2.3 | -1.8 | -1.3 | V |
| Gate Quiescent Voltage | $V_{DS} = 28$ V, $I_D = 225$ mA | V_{GSQ} | -2.0 | -1.5 | -1.0 | V |
| On Resistance | $V_{GS} = 2$ V, $I_D = 60$ mA | R_{ON} | — | 0.44 | 0.55 | Ω |
| Drain Current | $V_{DS} = 7$ V pulsed, pulse width 300 μs 0.2% Duty Cycle, $V_{GS} = 2$ V | I_D | — | 5.4 | — | A |

Absolute Maximum Ratings^{2,3,4}

| Parameter | Absolute Maximum |
|--|------------------|
| Drain Source Voltage, V_{DS} | 100 V |
| Gate Source Voltage, V_{GS} | -10 to 3 V |
| Gate Current, I_G | 40 mA |
| Total Device Power Dissipation (derated above +25°C) | 44 W |
| Junction Temperature, T_J | +200°C |
| Operating Temperature | -40°C to +85°C |
| Storage Temperature | -65°C to +150°C |

2. Exceeding any one or combination of these limits may cause permanent damage to this device.
3. MACOM does not recommend sustained operation near these survivability limits.
4. Operating at nominal conditions with $T_J \leq 200^\circ\text{C}$ will ensure $\text{MTTF} > 1 \times 10^6$ hours.

Thermal Characteristics⁵

| Parameter | Test Conditions | Symbol | Typical | Units |
|--------------------|--|-----------------|---------|-------|
| Thermal Resistance | $V_{DS} = 28 \text{ V}, T_J = 180^\circ\text{C}$ | $R_{\theta JC}$ | 4.0 | °C/W |

5. Junction temperature (T_J) measured using IR Microscopy. Case temperature measured using thermocouple embedded in heat-sink.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Nitride Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these MM Class A, CDM Class IV, HBM Class 1B devices.

Load-Pull Data, Reference Plane at Device Leads: $V_{DS} = 28\text{ V}$, $I_{DQ} = 225\text{ mA}$, $T_A = 25^\circ\text{C}$

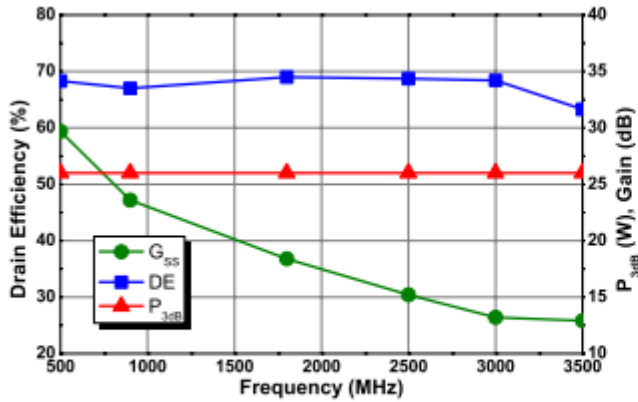


Figure 1 - Typical CW Performance in Load-Pull, $V_{DS} = 28\text{V}$, $I_{DQ} = 225\text{mA}$

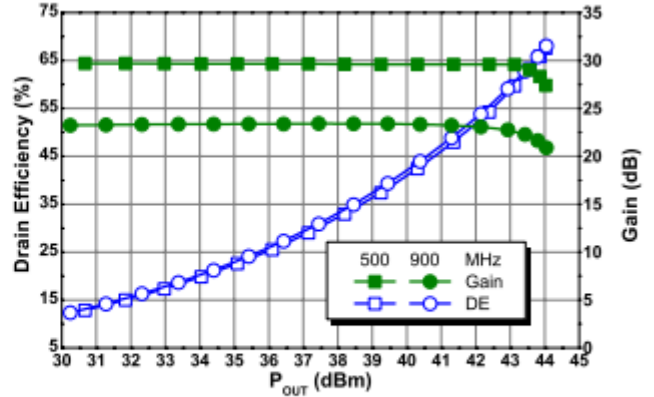


Figure 2 - Typical CW Performance¹ in Load-Pull, $V_{DS} = 28\text{V}$, $I_{DQ} = 225\text{mA}$

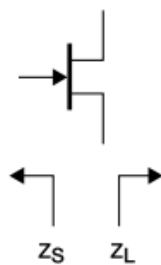
Load-Pull Data, Reference Plane at Device Leads: $V_{DS} = 28\text{ V}$, $I_{DQ} = 225\text{ mA}$, $T_C = 25^\circ\text{C}$

Table 1: Optimum Impedance Characteristics for CW Gain, Drain Efficiency, and Output Power Performance

| Frequency (MHz) | V_{DS} (V) | Z_S (Ω) | Z_L (Ω) | P_{SAT} (W) | GSS (dB) | Drain Efficiency @ P_{SAT} (%) |
|------------------|--------------|--------------------|--------------------|---------------|----------|----------------------------------|
| 500 ⁶ | 14 | 7.0 + j8.2 | 8.6 + j7.4 | 12 | 27.8 | 76 |
| 500 ⁶ | 22 | 7.0 + j8.2 | 9.7 + j11.3 | 21 | 29.2 | 74 |
| 500 ⁶ | 28 | 7.0 + j8.2 | 9.7 + j14.1 | 26 | 29.7 | 68 |
| 900 ⁶ | 14 | 5.8 + j3.1 | 6.8 + j4.7 | 12 | 22.4 | 74 |
| 900 ⁶ | 22 | 5.8 + j3.1 | 9.6 + j5.3 | 24 | 23.3 | 74 |
| 900 ⁶ | 28 | 5.8 + j3.1 | 9.8 + j7.8 | 26 | 23.6 | 67 |
| 1800 | 28 | 3.5 - j3.6 | 6.9 + j2.0 | 26 | 18.4 | 69 |
| 2500 | 14 | 3.9 - j7.5 | 6.2 - j8.0 | 13 | 13.7 | 70 |
| 2500 | 22 | 4.8 - j7.0 | 5.5 - j4.1 | 19 | 14.9 | 69 |
| 2500 | 28 | 4.8 - j7.0 | 5.5 - j4.1 | 26 | 15.2 | 69 |
| 3000 | 28 | 5.3 - j8.8 | 5.3 - j6.4 | 26 | 13.2 | 66 |
| 3500 | 28 | 5.0 - j14.5 | 7.0 - j9.5 | 26 | 12.9 | 63 |

6. 500 MHz and 900 MHz Load-Pull data collected using a 4.7 Ω resistor in the RF path added for stability.

Impedance Reference



Z_S is the source impedance presented to the device.
 Z_L is the load impedance presented to the device.

Z_S and Z_L vs. Frequency

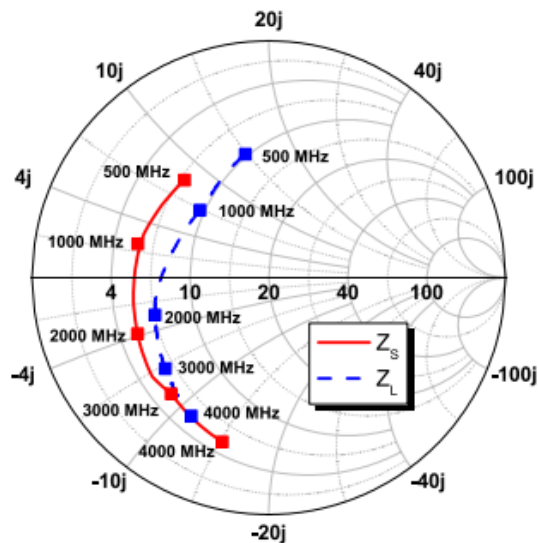


Figure 3 - Optimum Impedances for CW Performance, $V_{DS} = 28\text{V}$

Load-Pull Data, Reference Plane at Device Leads: $V_{DS} = 28\text{ V}$, $I_{DQ} = 225\text{ mA}$, $T_A = 25^\circ\text{C}$

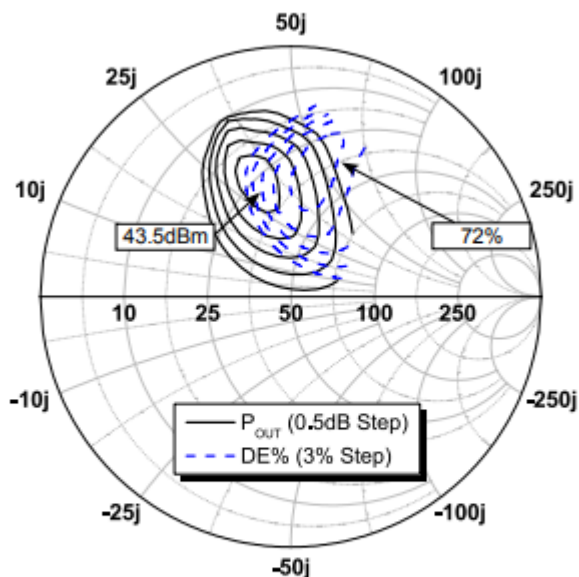


Figure 4 - Load-Pull Contours¹, 500MHz,
 $P_{IN} = 14.5\text{dBm}$, $Z_S = 7.0 + j8.2\ \Omega$

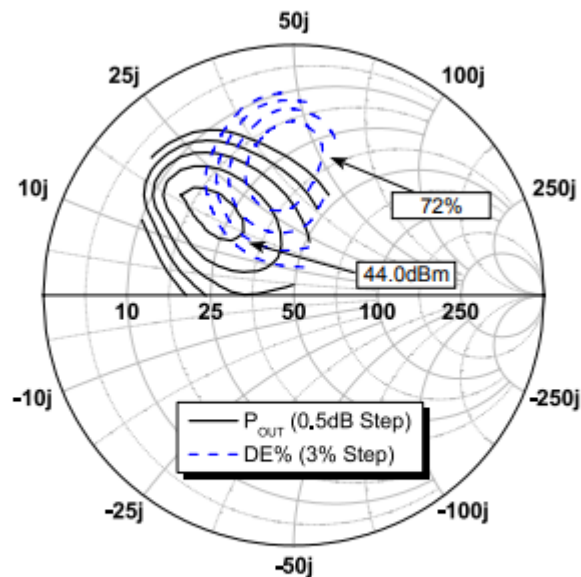


Figure 5 - Load-Pull Contours¹, 900MHz,
 $P_{IN} = 21.0\text{dBm}$, $Z_S = 5.8 + j3.1\ \Omega$

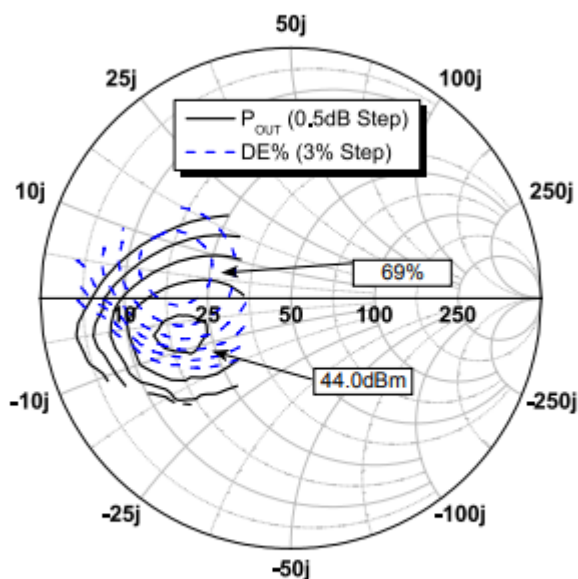


Figure 6 - Load-Pull Contours, 1800MHz,
 $P_{IN} = 26.5\text{dBm}$, $Z_S = 3.5 - j3.6\ \Omega$

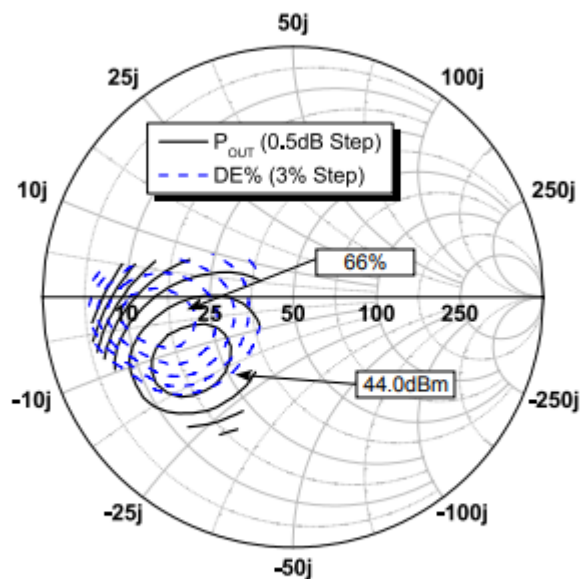


Figure 7 - Load-Pull Contours, 2500MHz,
 $P_{IN} = 29.4\text{dBm}$, $Z_S = 4.8 - j7.0\ \Omega$

Load-Pull Data, Reference Plane at Device Leads: $V_{DS} = 28\text{ V}$, $I_{DQ} = 225\text{ mA}$, $T_A = 25^\circ\text{C}$

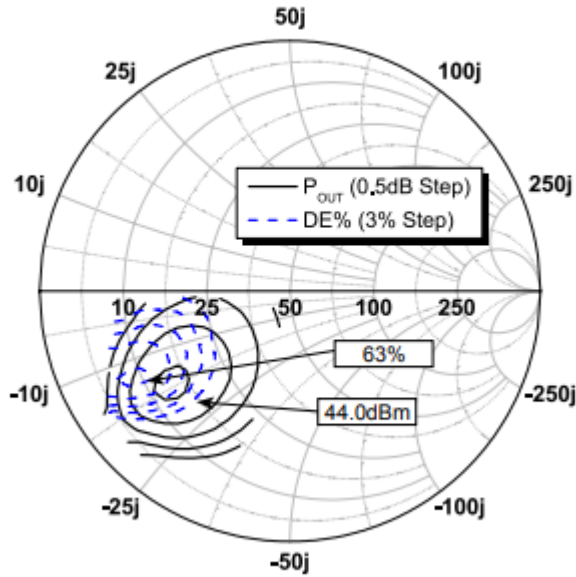


Figure 8 - Load-Pull Contours, 3000MHz,
 $P_{IN} = 31.7\text{dBm}$, $Z_S = 5.3 - j8.8\ \Omega$

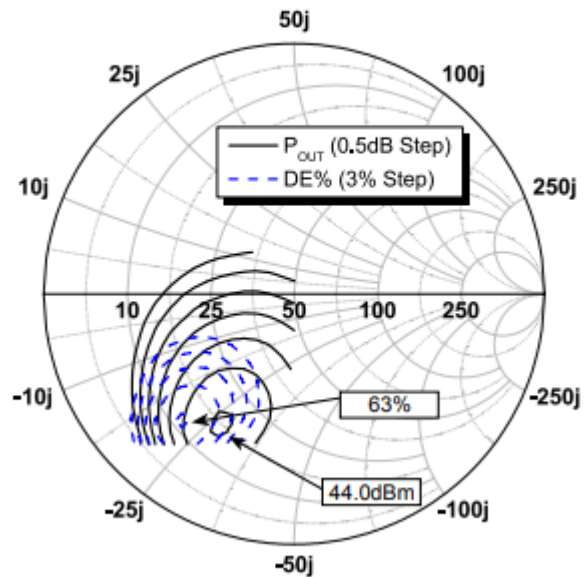


Figure 9 - Load-Pull Contours, 3500MHz,
 $P_{IN} = 33.5\text{dBm}$, $Z_S = 5.0 - j14.5\ \Omega$

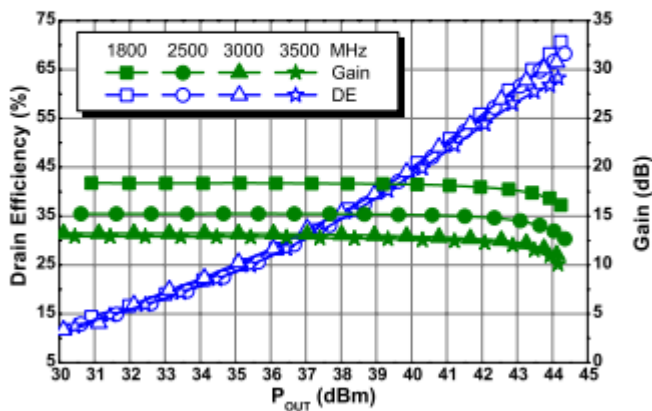


Figure 10 - Typical CW Performance in Load-Pull

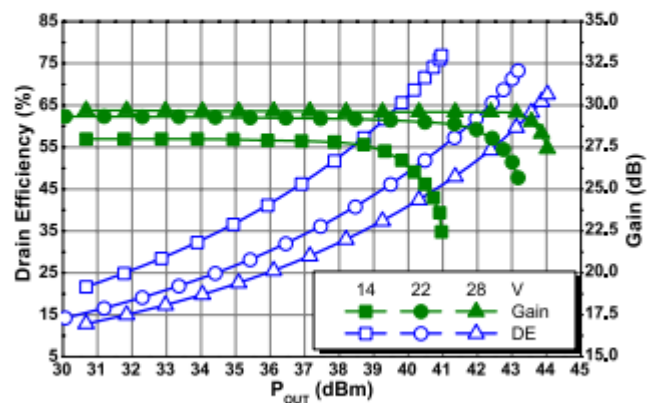


Figure 11 - Typical CW Performance¹ Over Voltage in Load-Pull, 500MHz

Load-Pull Data, Reference Plane at Device Leads: $V_{DS} = 28\text{ V}$, $I_{DQ} = 225\text{ mA}$, $T_A = 25^\circ\text{C}$

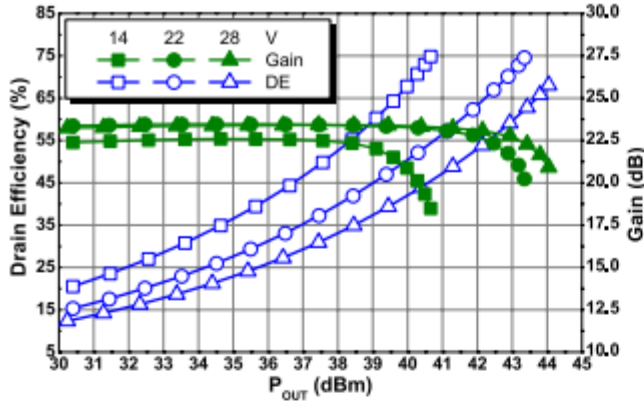


Figure 12 - Typical CW Performance¹ Over Voltage in Load-Pull, 900MHz

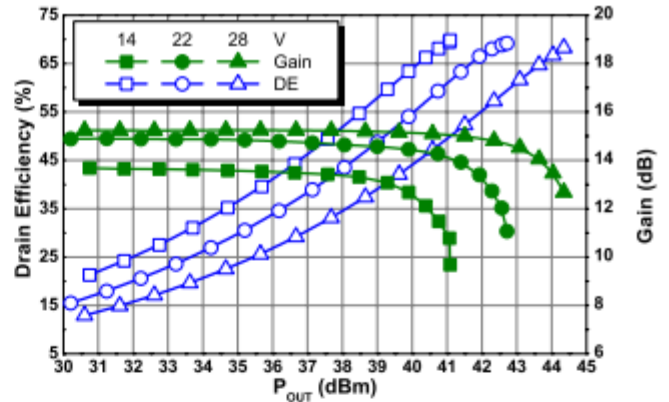


Figure 13 - Typical CW Performance Over Voltage in Load-Pull, 2500MHz

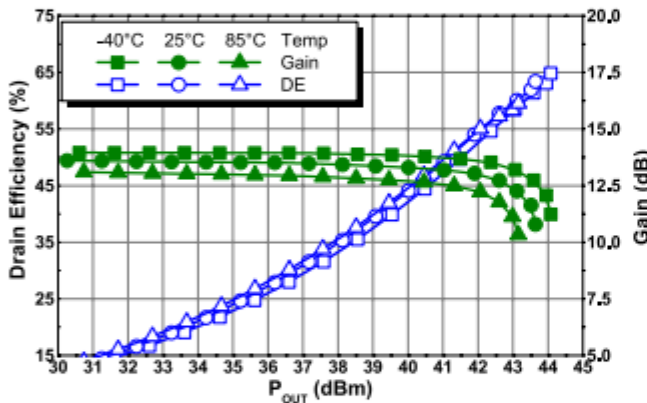


Figure 14 - Typical CW Performance Over Temperature in Nitronex Test Fixture, 3000MHz

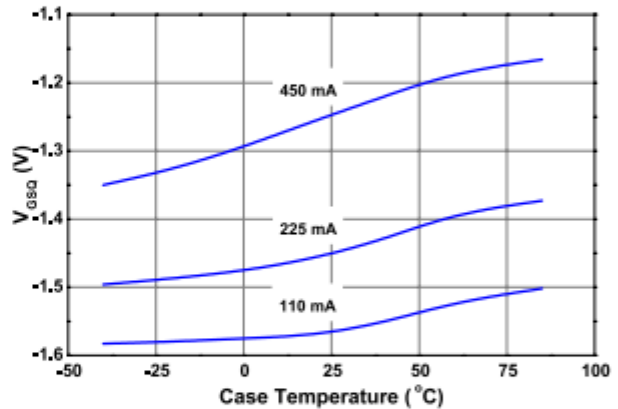


Figure 15 - Quiescent Gate Voltage (V_{GSQ}) Required to Reach I_{DQ} as a Function of Case Temperature, $V_{DS} = 28\text{ V}$

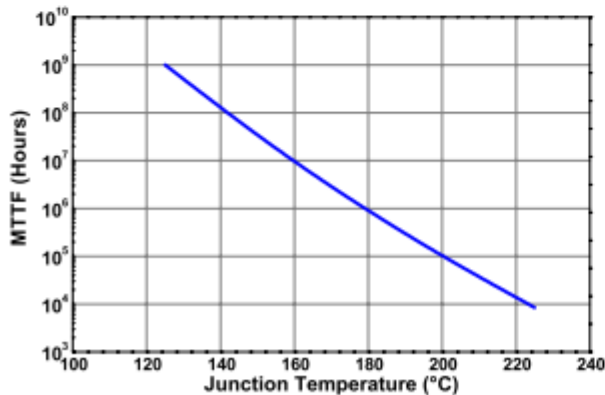


Figure 16 - MTTF of NRF1 Devices as a Function of Junction Temperature

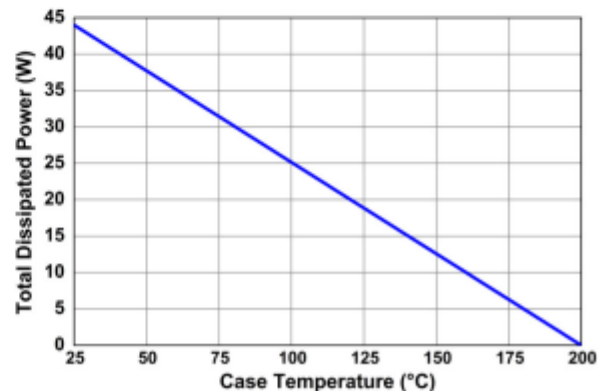
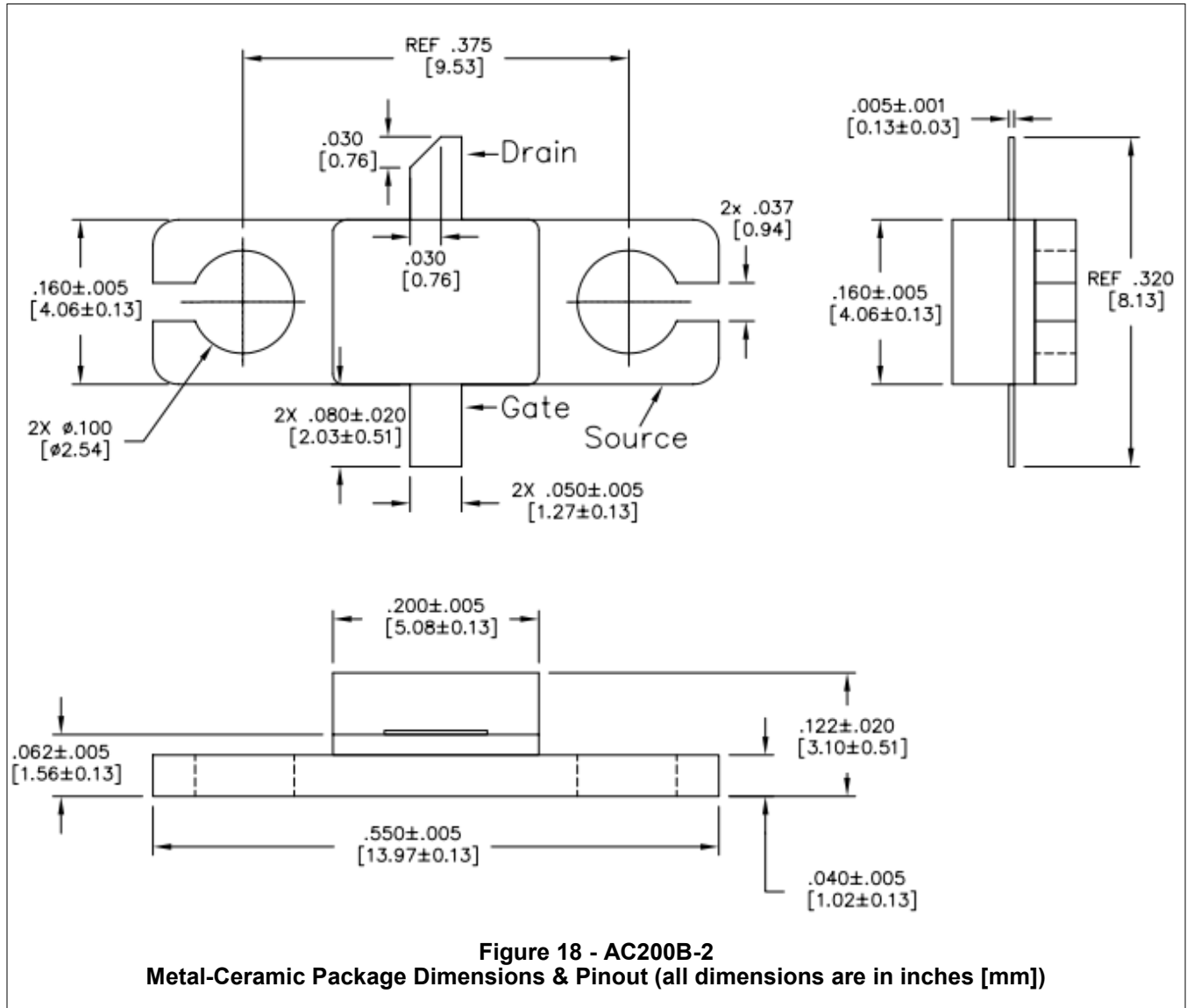


Figure 17 - Power Derating Curve

Outline Drawing



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